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AND AGEN DEPARTMEN	ICIES C	F THE			DRAWING APPROVAL DATE 93-04-09			SIZ		T	E CC			59	962-	9310	66			
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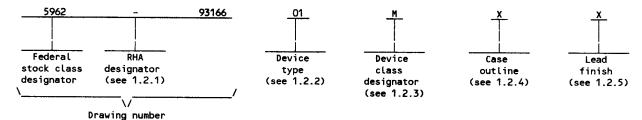
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<u>DISTRIBUTION STATEMENT A</u>. Approved for public release; distribution is unlimited.

5962-E266-93

## 1. SCOPE

- 1.1 <u>Scope</u>. This drawing forms a part of a one part one part number documentation system (see 6.6 herein). Two product assurance classes consisting of military high reliability (device classes B, Q, and M) and space application (device classes S and V) and a choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). Device class M microcircuits represent non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices". When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.
  - 1.2 PIN. The PIN shall be as shown in the following example:



- 1.2.1 RHA designator. Device classes M, B, and S RHA marked devices shall meet the MIL-M-38510 specified RHA levels and shall be marked with the appropriate RHA designator. Device classes Q and V RHA marked device shall meet the MIL-I-38535 specified RHA levels and shall be marked with the appropriate RHA designator. A dash (-) indicates a non RHA device.
  - 1.2.2 <u>Device type(s)</u>. The device type(s) shall identify the circuit function as follows:

Device type	Generic number 1/	Circuit function	Access time
01		32K x 8 PROM	55 ns
02		32K x 8 PROM	45 ns
03		32K x 8 PROM	35 ns
04		32K x 8 PROM	55 ns
05		32K x 8 PROM	45 ns
06		32K x 8 PROM	35 ns

1.2.3 <u>Device class designator</u>. The device class designator shall be a single letter identifying the product assurance level as follows:

1.2.4 <u>Case outline(s)</u>. The case outline(s) shall be as designated in MIL-STD-1835 and as follows:

Outline letter	<u>Descriptive designator</u>	<u>Terminals</u>	Package style
X	GDIP4-T28 or CDIP3-T28	28	Dual-in-line
Y	GDFP2-F28	28	Flat pack
Z	CQCC1-N32	32	Rectangular leadless chip carrier
U	GDIP1-T28 or CDIP2-T28	28	Dual-in-line

1.2.5 <u>Lead finish</u>. The lead finish shall be as specified in MIL-M-38510 for classes M, B, and S or MIL-I-38535 for classes Q and V. Finish letter "X" shall not be marked on the microcircuit or its packaging. The "X" designation is for use in specifications when lead finishes A, B, and C are considered acceptable and interchangeable without preference.

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1.3 Absolute maximum ratings. 2/			
Supply voltage range DC voltage applied to outputs in high Z state			
DC input voltage	3.0 V de	to +7.0 V dc	
DC program voltage			
Lead temperature (soldering, 10 seconds maxim	num) +260°C		
Thermal resistance, junction-to-case (O <sub>JC</sub> ) - Junction temperature (T <sub>J</sub> )	+175°C	ככםו-עופ	
Storage temperature ranĝe Temperature under bias		+150°C +125°C	
Data Retention			
1.4 Recommended operating conditions.			
Supply voltage (V <sub>CC</sub> )	4.5 V dc	to 5.5 V dc	
Ground voltage (GND)	0.0 V DC	minimum	
Supply voltage (V <sub>CC</sub> ) Ground voltage (GND)	0.8 V dc	maximum	
1.5 Logic testing for device classes Q and V.		+125°C	
Fault coverage measurement of manufacturing logic tests (MIL-STD-883, test method 5012)	XX perce	nt <u>4</u> /	
2. APPLICABLE DOCUMENTS			
2.1 Government specifications, standards, bulletin, ar	d handbook. Unles	s otherwise specified, the	e following
specifications, standards, bulletin, and handbook of the of Specifications and Standards specified in the solicite			
herein.	icion, torm a part	or time training to the tr	он оросни
SPECIFICATION			
MILITARY			
MIL-M-38510 - Microcircuits, General Spec MIL-I-38535 - Integrated Circuits, Manufa		specification for.	
STANDARDS			
MILITARY			
MIL-STD-480 - Configuration Control-Engir			
MIL-STD-883 - Test Methods and Procedures MIL-STD-1835 - Microcircuit Case Outlines.		itcs.	
BULLETIN			
POFFELIA			
MILITARY			
MIL-BUL-103 - List of Standardized Mili	tary Drawings (SMD	s).	
1/ Generic numbers are listed on the Standardiz	ed Military Drawin	g Source Approval Bulletin	1
and will also be listed in MIL-BUL-103.  2/ Stresses above the absolute maximum rating m	my cause permanent	damage to the device. Ex	tended operation
at the maximum levels may degrade performanc 3/ Must withstand the added P <sub>p</sub> due to short cir	e and affect relia	bility. t \	
$3/$ Must withstand the added $P_D$ due to short cir $\overline{4}/$ When a Qualified Manufacturers' List (QML) s	ource exists, a va	'OS'' lue will be provided.	
STANDARDIZED	SIZE		5962-93166
MILITARY DRAWING	A		
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		DRIVE CT ON THE	OTTER TO
DELICH, CHIC TOTT		REVISION LEVEL	SHEET

## HANDBOOK

MILITARY

MIL-HDBK-780 - Standardized Military Drawings.

(Copies of the specification, standard, and bulletin required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

2.2 <u>Non-Government publications</u>. The following documents form a part of this document to the extent specified herein. Unless otherwise specified, the issues of the documents which are DoD adopted are those listed in the issue of the DODISS cited in the solicitation. Unless otherwise specified, the issues of documents not listed in the DODISS are the issues of the documents cited in the solicitation.

AMERICAN SOCIETY FOR TESTING AND MATERIALS (ASTM)

ASTM Standard F1192-88 - Standard Guide for the Measurement of Single Event Phenomena from Heavy Ion Irradiation of Semiconductor Devices.

(Applications for copies of ASTM publications should be addressed to the American Society for Testing and Materials, 1916 Race Street, Philadelphia, PA 19103).

ELECTRONICS INDUSTRIES ASSOCIATION (EIA)

JEDEC Standard No. 17 - A Standardized Test Procedure for the Characterization of Latch-up in CMOS Integrated Circuits.

(Applications for copies should be addressed to the Electronics Industries Association, 2001 Eye Street, N.W., Washington, DC 20006.)

(Non-Government standards and other publications are normally available from the organizations that prepare or distribute the documents. These documents also may be available in or through libraries or other informational services.)

2.3 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

## 3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements for device class M shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein. The individual item requirements for device classes B and S shall be in accordance with MIL-M-38510 and as specified herein. For device classes B and S, a full electrical characterization table for each device type shall be included in this SMD. The individual item requirements for device classes Q and V shall be in accordance with MIL-I-38535, the device manufacturer's Quality Management (QM) plan, and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-M-38510 for device classes M, B, and S and MIL-I-38535 for device classes Q and V and herein.
  - 3.2.1 <u>Case outline(s)</u>. The case outline(s) shall be in accordance with 1.2.4 herein.
- 3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.
- 3.2.3 Truth table. The truth table shall be as specified on figure 2.
- 3.2.3.1 <u>Unprogrammed devices</u>. The truth table for unprogrammed devices for contracts involving no altered item drawing shall be as specified on figure 2 herein. When required in screening (see 4.2 herein) or qualification conformance inspection groups A, B, C, or D (see 4.4 herein), the devices shall be programmed by the manufacturer prior to test. A minimum of 50 percent of the total number of cells shall be programmed or at least 25 percent of the total number of cells to any altered item drawing.
- 3.2.3.2 <u>Programmed devices</u>. The truth tables for programmed devices shall be as specified by an attached altered item drawing.

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Test	Symbol	Condition -55°C ≤ T <sub>C</sub> ±	≤ +125°C	Group A	Device	Li	mit	t Unit	
		$4.5 \text{ V} \leq \text{V}_{CC}^{-} \leq 5.5 \text{ V}$ unless otherwise specified		subgroups	type	Min	Max		
Output high voltage	v <sub>он</sub>	v <sub>CC</sub> = 4.5 v, I <sub>OH</sub> v <sub>IN</sub> = v <sub>IH</sub> , v <sub>IL</sub>	= -2.0 mA,	1,2,3	ALL	2.4		v	
Output low voltage	v <sub>oL</sub>	V <sub>CC</sub> = 4.5 V, I <sub>OL</sub> V <sub>IN</sub> = V <sub>IH</sub> , V <sub>IL</sub>	= 6.0 mA,				0.4		
Input high voltage <u>1</u> /	v <sub>IH</sub>					2.0			
Input low voltage 1/	v <sub>IL</sub>						0.8		
Input leakage current	IIX	GND $\leq$ V <sub>IN</sub> $\leq$ V <sub>CC</sub>				-10	+10	μΑ	
Output leakage current	I <sub>OZ</sub>	GND < VOUT < VCC	·			-40	+40		
Output short circuit current <u>2</u> / <u>3</u> /	Ios	v <sub>cc</sub> = 5.5 v, v <sub>ou</sub>	T = 0.0 V			-20	-90	mA	
Power supply current	Icc	V <sub>CC</sub> = 5.5 V, I <sub>OU</sub> V <sub>IN</sub> = 0 to 3.0 V f = f <sub>MAX</sub> 4/5/	T = O mA,				130		
Standby supply current	I <sub>SB</sub>	V <sub>CC</sub> = 5.5 V, CS <sub>1</sub> I <sub>OUT</sub> = 0 mA, V <sub>IN</sub>	≥ V <sub>IB</sub> ′v				40		
Input capacitance $3/$	CIN	V <sub>CC</sub> = 5.0 V, T = 25°C, f = 1 (see 4.4.1c)	MHz,	4			10	pF	
Output capacitance 3/	Соит	V <sub>CC</sub> = 5.0 V, T = 25°C, f = 1 (see 4.4.1c)	MHz	4			10		
Functional testing		See 4.4.1d		7,8A,8B					
Address to output valid	t <sub>AA</sub>	See figures 3 ar	nd 4 and	9,10,11	01,04		55	ns	
					02,05		45	-	
potnotes at end of table				<u> </u>	03,06		35	1	
STANDARI MILITARY I			SIZE				59	62-93	
DEFENSE ELECTRONIC DAYTON, OHIO	S SUPPL		A		SION I	B118-	SHE		

Test	Symbol	Conditions $-55^{\circ}C \leq T_{C} \leq +125^{\circ}C$	Group A	Device			
		-55°C ≤ T <sub>C</sub> ≤ +125°C 4.5 V ≤ V <sub>CC</sub> ≤ 5.5 V unless otherwise specified	subgroups	type	Min	Max	
Chip sel <u>ec</u> t inactive to high Z (CS <sub>1</sub> and CS <sub>2</sub> only)	t <sub>HZCS</sub>	See figures 3 and 4 and note <u>6</u> /	9,10,11	01,02		30	ns
3/ 7/		110te <u>u</u> 7		03		25	
Output enable inactive to	t <sub>HZOE</sub>			04		30	
high Z <u>3</u> / <u>7</u> /				05,06		25	
Chip select ac <u>ti</u> ve to	tacs			01,02		30	
output valid (CS <sub>1</sub> and CS <sub>2</sub> only)				03	- 1 - 5	25	
Output enable active to	t <sub>OE</sub>			04		30	
output valid				05,06		25	1
Chip enable inactive to	t			01,04		60	
high Z (CE only) <u>3</u> / <u>7</u> /	<sup>t</sup> HZCE			02,05		50	
				03,06		40	
Chip enable ac <u>ti</u> ve to	•			01,04		60	
output valid (CE only)	<sup>t</sup> ACE		:	02,05		50	
				03,06		40	
Chip enable active to power up <u>3</u> /	t <sub>PU</sub>			ALL	0		
Chip enable inactive to	t <sub>PD</sub>			01,04		60	
power down <u>3</u> /				02,05		50	1
	ļ <del> </del>			03,06		40	
Output hold from address change <u>3</u> /	<sup>t</sup> oн			ALL	0		

<sup>1/</sup> These are absolute values with respect to device ground and all overshoots and undershoots due to system or tester noise are included.

to the limits specified in table I.

At  $f = f_{MAX}$ , the inputs are switching at  $1/t_{AA}$ .

Devices 01-03 CE = 0.0 V,  $\overline{CS}_1 = 3.0$  V,  $CS_2 = 0.0$  V; devices 04-06 CE = 0.0 V,  $\overline{OE} = 3.0$  V.

AC tests are performed with input rise and fall times of 5 ns or less, timing reference levels of 1.5 V, input pulse

levels of 0 to 3.0 V, and the output load on figure 4, circuit A.

Transition is measured at steady-state high level -500 mV or steady-state low level +500 mV on the output from the 1.5 V level on the input with the output load on figure 4, circuit B.

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For test purposes, not more than one output at a time should be shorted. Short circuit test duration should not exceed thirty seconds.

Tested initially and after any design or process changes that affect that parameter, and therefore shall be guaranteed

Device Types	01 -	- 03	04 -	- 06
Case Outlines	X,Y	Z	U	Z
Terminal Number	Termina	l Symbol	Terminal	. Symbol
1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 17 18 19 20 21 22 23 24 25 26 27 28 29 30 31 31 31 32 31 32 32 32 32 32 32 32 32 32 32 32 32 32	98765430100100 34567 ES US 43 21001	NA AAAAAAAA OO OO OO OO OO OO OO AAAAAAAA	PP 0 PA 7 6 5 4 5 0 1 0 0 1 0 0 0 0 0 0 0 0 0 0 0 0 0 0	NY 44444 A 4 4 4 6 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0

FIGURE 1. <u>Terminal connections</u>.

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# Devices 01 - 03

State	Mode	cs <sub>2</sub>	cs <sub>1</sub>	CE	A <sub>14</sub> - A <sub>0</sub>	Power	Outputs
Programmed	Read	V <sub>IH</sub>	VIL	v <sub>IL</sub>	х	<sup>I</sup> cc	Data out
	Standby	х	Х	v <sub>IH</sub>	х	I <sub>SB</sub>	High Z
	Output disable	х	v <sub>IH</sub>	х	х	Icc	High Z
	Output disable	VIL	X	х	x	Icc	High Z
Unprogrammed	Blank check ones	VIHP	V <sub>PP</sub>	VILP	х	<sup>I</sup> cc	Ones
	Blank check zeros	VILP	V <sub>PP</sub>	VILP	х	<sup>1</sup> cc	Zeros

# Devices 04 - 06

State	Mode	CE	ŌĒ	V <sub>PP</sub>	A <sub>14</sub> - A <sub>0</sub>	Power	Outputs
Programmed	Read	VIL	VIL	Х	Х	1 <sub>cc</sub>	Data out
	Standby	VIH	х	Х	x	1 <sub>SB</sub>	High Z
	Output disable	х	v <sub>IH</sub>	Х	х	1 <sub>CC</sub>	High Z
Unprogrammed	Blank check ones	VIHP	VILP	V <sub>PP</sub>	х	Icc	Ones
	Blank check zeros	VILP	VILP	V <sub>PP</sub>	х	<sup>I</sup> cc	Zeros

NOTES:
1. X = Don't care
2. High Z = High-impedance state

# FIGURE 2. <u>Truth table</u>

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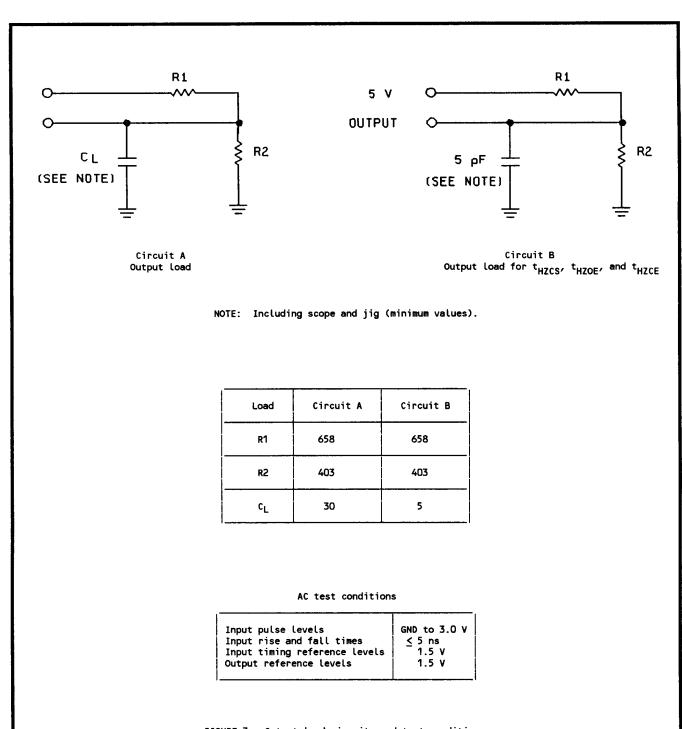
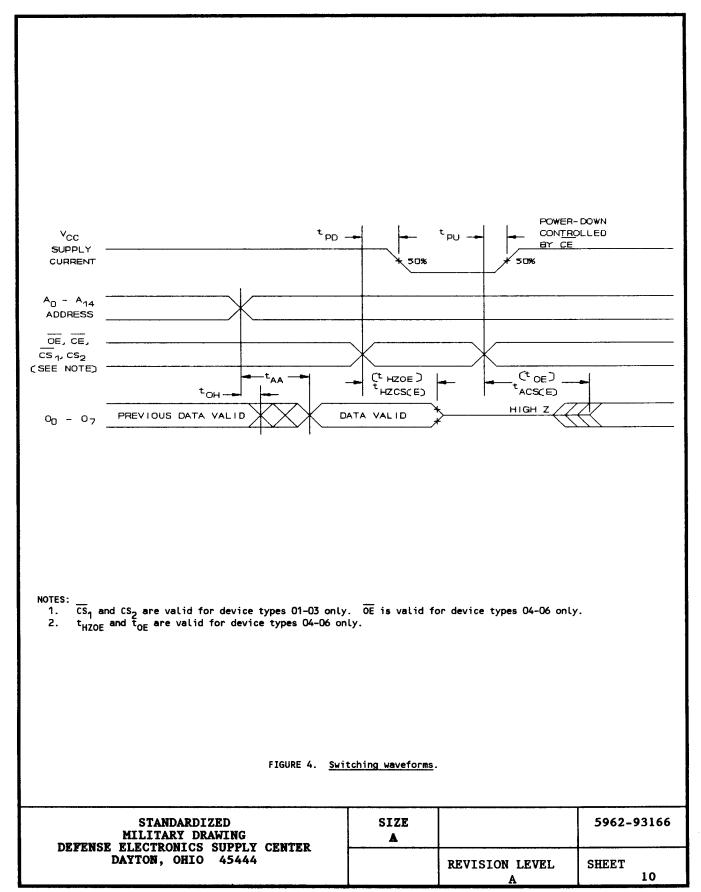


FIGURE 3. Output load circuits and test conditions.

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- 3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified, the electrical performance characteristics, and postirradiation parameter limits are as specified in table I and shall apply over the full case operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are described in table I.
- 3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. Marking for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein). In addition, the manufacturer's PIN may also be marked as listed in MIL-BUL-103. Marking for device classes B and S shall be in accordance with MIL-M-38510. Marking for device classes Q and V shall be in accordance with MIL-I-38535.
- 3.5.1 <u>Certification/compliance mark</u>. The compliance mark for device class M shall be a "C" as required in MIL-STD-883 (see 3.1 herein). The certification mark for device classes B and S shall be a "J" or "JAN" as required in MIL-M-38510. The certification mark for device classes Q and V shall be a "QML" as required in MIL-I-38535.
- 3.6 <u>Certificate of compliance</u>. For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-BUL-103 (see 6.7.3 herein). For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.7.2 herein). The certificate of compliance submitted to DESC-EC prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device class M the requirements of MIL-STD-883 (see 3.1 herein), or for device classes Q and V, the requirements of MIL-I-38535 and the requirements herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device class M in MIL-STD-883 (see 3.1 herein) or device classes B and S in MIL-M-38510 or for device classes Q and V in MIL-I-38535 shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 Notification of change for device class M. For device class M, notification to DESC-EC of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-480.
- 3.9 <u>Verification and review for device class M</u>. For device class M, DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
- 3.10 <u>Microcircuit group assignment for device classes M, B, and S</u>. Device classes M, B, and S devices covered by this drawing shall be in microcircuit group number 42 (see MIL-M-38510, appendix E).
- 3.10.1 <u>Processing options</u>. Since the device is capable of being programmed by either the manufacturer or the user to result in a wide variety of configurations, two processing options are provided for selection in the contract using an altered item drawing.
- 3.10.2 <u>Unprogrammed device delivered to the user</u>. All testing shall be verified through group A testing as defined in 3.2.3.1 and table IIA. It is recommended that users perform subgroups 7 and 9 after programming to verify the specific program configuration.
- 3.10.3 Manufacturer-programmed device delivered to the user. All testing requirements and quality assurance provisions herein, including the requirements of the altered item drawing, shall be satisfied by the manufacturer prior to delivery.
- 3.11 <u>Serialization for device class S and V</u>. All device class S devices shall be serialized in accordance with MIL-M-38510. Class V shall be serialized in accordance with MIL-I-38535.
  - 4. QUALITY ASSURANCE PROVISIONS
- 4.1 <u>Sampling and inspection</u>. For device class M, sampling and inspection procedures shall be in accordance with section 4 of MIL-M-38510 to the extent specified in MIL-STD-883 (see 3.1 herein). For device classes B and S, sampling and inspection procedures shall be in accordance with MIL-M-38510 and method 5005 of MIL-STD-883, except as modified herein. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-I-38535 and the device manufacturers' QM plan.

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TABLE IIA. Electrical test requirements.  $\underline{1}/\underline{2}/\underline{3}/\underline{4}/\underline{5}/\underline{6}/\underline{7}/\underline{8}/\underline{1}$ 

Line	Test	(in accor	Subgroups dance with MIL- method 5005, ta	-STD-883, able I)	(in accord	roups dance with , table III)
no.	requirements	Device class M	Device class B	Device class S	Device class Q	Device class V
1	Interim electrical parameters (see 4.2)		1,7,9 or 2,8A,10	1,7,9 or 2,8A,10		1,7,9 or 2,8A,10
2	Static burn-in I and II (method 1015)	Not required	Not required	Required	Not required	Required
3	Same as line 1			1*,7* <u>A</u>		1*,7* <u>\</u>
4	Dynamic burn-in (method 1015)	Required	Required	Required	Required	Required
5	Same as line 1			1*,7* A		1*,7* A
6	Final electrical parameters (programmed_devices)	1*,2,3,7*, 8A,8B,9,10, 11	1*,2,3,7*, 8A,8B,9,10, 11	1*,2,3,7*, 8A,8B,9,10, 11	1*,2,3,7*, 8A,8B,9,10, 11	  1*,2,3,7*,  8A,8B,9,10,  11
6A	Final electrical parameters (unprogrammed devices)	1*,2,3,7*, 8A,8B	1*,2,3,7*, 8A,8B	1*,2,3,7*, 8A,8B	1*,2,3,7*, 8A,8B	1*,2,3,7*, 8A,8B
7	Group A test requirements	1,2,3,4**,7, 8A,8B,9,10,11	1,2,3,4**,7, 8A,8B,9,10,11	1,2,3,4**,7, 8A,8B,9,10,11	1,2,3,4**,7, 8A,8B,9,10,11	1,2,3,4**,7, 8A,8B,9,10,11
8	Group B end-point electrical parameters			   1,2,3,7,8A,   8A,8B,9,   10,11 Δ		
9	Group C end-point electrical parameters	2,3,7, 8A,8B	1,2,3,7, 8A,8B Δ		1,2,3,7, 8A,8B Δ	1,2,3,7,8A, 8B,9,10,11
10	Group D end-point electrical parameters	2,3, 8A,8B	2,3, 8A,8B	2,3, 8A,8B	2,3, 8A,8B	2,3, 8A,8B
11	Group E end-point electrical parameters	1,7,9	1,7,9	1,7,9	1,7,9	1,7,9

- Blank spaces indicate tests are not applicable.
- Any or all subgroups may be combined when using high-speed testers.
- Subgroups 7 and 8 functional tests shall verify the truth table.
- $\star$  indicates PDA applies to subgroup 1 and 7.
- \*\* see 4.4.1c.
- 1/2/3/45/6/  $\Delta$  indicates delta limit (see table IIB) shall be required where specified, and the delta values shall be computed with reference to the previous interim electrical parameters (line 1).
- 7/ See 4.6.

-			
8/	See	4.4	4.1e

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TABLE IIB. Delta limits at +25°C.

Test <u>1</u> /	Device types
IIX	±10 percent of specified value in table I
I <sub>OZ</sub>	±10 percent of specified value in table I

- 1/ The above parameter shall be recorded before and after the required burn-in and life tests to determine the delta.
- 4.2 <u>Screening</u>. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. For device classes B and S, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to qualification and quality conformance inspection. For device classes Q and V, screening shall be in accordance with MIL-I-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection.
  - 4.2.1 Additional criteria for device classes M, B, and S.
    - a. Delete the sequence specified as initial (preburn-in) electrical parameters through interim (postburn-in) electrical parameters of method 5004 and substitute lines 1 through 6 of table IIA herein.
    - b. For device class M, the test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. For device classes B and S, the test circuit shall be submitted to the qualifying activity. For device classes M, B, and S, the test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
      - (1) Static burn-in for device class S (method 1015 of MIL-STD-883, test condition A).
        - (a) All inputs shall be connected to GND. Outputs may be open or connected to 4.5 V minimum. Resistors R1 are optional on both inputs and outputs, and required on outputs connected to  $V_{CC}$  ±0.5 V. R1 = 220 $\Omega$  to 47 k $\Omega$ . For static II burn-in, reverse all input connections (i.e.,  $V_{SS}$  to  $V_{CC}$ ).
        - (b)  $V_{CC} = 4.5 \text{ V minimum}$ .
        - (c) Ambient temperature  $(T_A)$  shall be  $+125^{\circ}C$  minimum.
        - (d) Test duration for the static test shall be 48 hours minimum. The 48-hour burn-in shall be broken into two sequences of 24 hours each (static I and static II) followed by interim electrical measurements.
      - (2) Dynamic burn-in for device classes M, B, and S (method 1015 of MIL-STD-883, test condition D; for circuit, see
    - c. Interim and final electrical parameters shall be as specified in table IIA herein.
    - d. A data retention stress test shall be included as part of the screening procedure and shall consist of the following: (Steps 1 through 4 are performed at the wafer level.)
      - (1) Program 100 percent of the total number of cells, excluding the security bit.
      - (2) Bake, unbiased, for 72 hours at  $+140^{\circ}$ C or for 48 hours at  $+150^{\circ}$ C or for 8 hours at  $+200^{\circ}$ C, or 2 hours at  $+300^{\circ}$ C for unassembled devices only.
      - (3) Perform margin test using Vm = +5.7 V at +25°C using loose timing (i.e.,  $t_{AA} \ge 1 \mu s$ ).
      - (4) Erase.

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e. For classes S and B devices, post dynamic burn-in electrical parameter measurements may, at the manufacturer's option, be performed separately or included in the final electrical parameter requirements.

# 4.2.2 Additional criteria for device classes Q and V.

- a. The burn-in test duration, test condition, and test temperature or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-I-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
- b. Interim and final electrical test parameters shall be as specified in table IIA herein.
- c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in appendix B of MIL-I-38535.

## 4.2.3 Percent defective allowable (PDA).

- a. The PDA for class S devices shall be 5 percent for static burn-in and 5 percent for dynamic burn-in, based on the exact number of devices submitted to each separate burn-in.
- b. The PDA for class B devices shall be in accordance with MIL-M-38510 for dynamic burn-in.
- c. Static burn-in I and II failures shall be cumulative for determining PDA.
- d. Those devices whose measured characteristics, after burn-in, exceed the specified delta limits or electrical parameter limits specified in table I, subgroup 1, are defective and shall be removed from the lot. The verified failures divided by the total number of devices in the lot initially submitted to burn-in shall be used to determine the percent defective for the lot and the lot shall be accepted or rejected based on the specified PDA.
- e. The PDA for device classes Q and V shall be in accordance with MIL-I-38535 for dynamic burn-in.

## 4.3 Qualification inspection.

- 4.3.1 <u>Qualification inspection for device classes B and S</u>. Qualification inspection for device classes B and S shall be in accordance with MIL-M-38510. Inspections to be performed shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.5). Qualification data for subgroups 7, 8A, and 8B shall be attributes only.
- 4.3.1.1 <u>Qualification extension for device classes B and S</u>. When authorized by the qualifying activity, if a manufacturer qualifies one device type which is identical (i.e., same die) to other device types on this specification, the slower device types may be part I qualified, upon the request of the manufacturer, without any further testing. The faster device types may be part I qualified by performing only group A qualification testing.
- 4.3.2 <u>Qualification inspection for device classes Q and V</u>. Qualification inspection for device classes Q and V shall be in accordance with MIL-I-38535. Inspections to be performed shall be those specified in MIL-I-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.5).
- 4.4 <u>Conformance inspection</u>. Quality conformance inspection for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein) and as specified herein. Quality conformance inspection for device classes B and S shall be in accordance with MIL-M-38510 and as specified herein. Inspections to be performed for device classes M, B, and S shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.5). Technology conformance inspection for classes Q and V shall be in accordance with MIL-I-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-I-38535 permits alternate in-line control testing.

## 4.4.1 Group A inspection.

- a. Tests shall be as specified in table IIA herein.
- b. Subgroups 5 and 6 in table I, method 5005 of MIL-STD-883 shall be omitted.

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- c. Subgroup 4 (C<sub>IN</sub> and C<sub>OUT</sub> measurements) shall be measured only for initial qualification and after any process or design changes which may affect input or output capacitance. Capacitance shall be measured between the designated terminal and GND at a frequency of 1 MHz. Sample size is 15 devices with no failures, and all input and output terminals tested.
- d. For device class M, subgroups 7 and 8 tests shall be sufficient to verify the truth table. For device classes B and S, subgroups 7 and 8 tests shall be sufficient to verify the truth table as approved by the qualifying activity. For device classes Q and V, subgroups 7 and 8 shall include verifying the functionality of the device; these tests shall have been fault graded in accordance with MIL-STD-883, test method 5012 (see 1.5 herein).
- e. O/V (latch-up) tests shall be measured only for initial qualification and after any design or process changes which may affect the performance of the device. For device class M, procedures and circuits shall be maintained under document revision level control by the manufacturer and shall be made available to the preparing activity or acquiring activity upon request. For device classes B and S, the procedures and circuits shall be maintained under document revision control by the manufacturer and shall be made available to the qualifying activity upon request. For device classes Q and V, the procedures and circuits shall be shall be under the control of the device manufacturer's TRB in accordance with MIL-I-38535 and shall be made available to the preparing activity or acquiring activity upon request. Testing shall be on all pins, on five devices with zero failures. Latch-up test shall be considered destructive. Information contained in JEDEC Standard number 17 may be used for reference.
- f. Unprogrammed devices shall be tested for programmability and ac performance compliance to the requirements of group A, subgroups 9, 10, and 11. Either of two techniques is acceptable:
  - (1) Testing the entire lot using additional built-in test circuitry which allows the manufacturer to verify programmability and ac performance without programming the user array. If this is done, the resulting test patterns shall be verified on all devices during subgroups 9, 10, and 11, group A testing in accordance with the sampling plan specified in MIL-STD-883, method 5005.
  - (2) If such compliance cannot be tested on an unprogrammed device, a sample shall be selected to satisfy programmability requirements prior to performing subgroups 9, 10, and 11. Twelve devices shall be submitted to programming (see 3.2.3.2). If more than two devices fail to program, the lot shall be rejected. At the manufacturer's option, the sample may be increased to 24 total devices with no more than 4 total device failures allowable. Ten devices from the programmability sample shall be submitted to the requirements of group A, subgroups 9, 10, and 11. If more than two devices fail, the lot shall be rejected. At the manufacturer's option, the sample may be increased to 20 total devices with no more than 4 total device failures allowable.
- 4.4.2 <u>Group B inspection.</u> The group B inspection end-point electrical parameters shall be as specified in table IIA herein. For device class S steady-state life tests, the test circuit shall be submitted to the qualifying activity.
  - a. For device class S, steady-state life test circuits shall be conducted using test condition D and the circuit described in 4.2.1b herein, or equivalent as approved by the qualifying activity.
  - b. For device class S only, end-point electrical parameters shall be as specified in table IIA herein. Delta limits shall apply only to subgroup 5 of group B inspections and shall consist of tests specified in table IIB herein.
- 4.4.3 <u>Group C inspection</u>. The group C inspection end-point electrical parameters shall be as specified in table IIA herein. Delta limits shall apply only to subgroup 1 of group C inspection and shall consist of tests specified in table IIB herein.
  - 4.4.3.1 Additional criteria for device classes M and B. Steady-state life test conditions, method 1005 of MIL-STD-883:
    - a. Test condition D. For device class M, the test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. For device class B, the test circuit shall be submitted to the qualifying activity. For device classes M and B, the test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.
    - b.  $T_A = +125$ °C, minimum.
    - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

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- 4.4.3.2 Additional criteria for device classes Q and Y. The steady-state life test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-I-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.
- 4.4.4 <u>Group D inspection</u>. For group D inspection, end-point electrical parameters shall be as specified in table IIA herein.
- 4.4.5 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein). RHA levels for device classes B, S, Q, and V shall be M, D, R, and H and for device class M shall be M and D.
  - a. End-point electrical parameters shall be as specified in table IIA herein.
  - b. For device classes M, B, and S, the devices shall be subjected to radiation hardness assured tests as specified in MIL-M-38510 for the RHA level being tested. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-I-38535 for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T<sub>A</sub> = +25°C ±5°C, after exposure, to the subgroups specified in table IIA herein.
  - c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.
- 4.5 <u>Programming procedure</u>. The programming procedures shall be as specified by the device manufacturer and shall be made available upon request.
- 4.6 <u>Delta measurements for device classes B, S, Q, and V</u>. Delta measurements, as specified in table IIA, shall be made and recorded before and after the required burn-in screens and steady-state life tests to determine delta compliance. The electrical parameters to be measured, with associated delta limits are listed in table IIB. The device manufacturer may, at his option, either perform delta measurements or within 24 hours after burn-in perform final electrical parameter tests, subgroups 1, 7, and 9.
  - 5. PACKAGING
- 5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-M-38510 for device classes M, B, and S and MIL-I-38535 for device classes Q and V.
  - 6. NOTES
- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
- 6.1.2 <u>Substitutability</u>. Device classes B and Q devices will replace device class M devices.
- 6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-481 using DD Form 1693, Engineering Change Proposal (Short Form).
- 6.3 <u>Record of users</u>. Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and the applicable SMD. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronics devices (FSC 5962) should contact DESC-ECS, telephone (513) 296-6047.
  - 6.4 Comments . Comments on this drawing should be directed to DESC-ECS, Dayton, Ohio 45444, or telephone 513-296-5377.

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6.5	Symbols,			definitions, and functional descriptions.														
C,	N -																	Input terminal capacitance.
ςō	IIT																	Output terminal capacitance.
I	r.			-	-	-	-	-	-									Supply current.
Ϊ́	ζ.																	Input current.
																		Output current.
																		Case temperature.

. . . . . . . . . . . . . . . Positive supply voltage (5.0 V). . . . . . . . . . . . . . . . Ground zero voltage potential.

6.6 One part - one part number system. The one part - one part number system described below has been developed to allow for transitions between identical generic devices covered by the four major microcircuit requirements documents (MIL-M-38510, MIL-H-38534, MIL-I-38535, and 1.2.1 of MIL-STD-883) without the necessity for the generation of unique PIN's. The four military requirements documents represent different class levels, and previously when a device manufacturer upgraded military product from one class level to another, the benefits of the upgraded product were unavailable to the Original Equipment Manufacturer (OEM), that was contractually locked into the original unique PIN. By establishing a one part number system covering all four documents, the OEM can acquire to the highest class level available for a given generic device to meet system needs without modifying the original contract parts selection criteria.

Military documentation format	Example PIN under new system	Manufacturing source listing	Document <u>Listing</u>
New MIL-M-38510 Military Detail Specifications (in the SMD format)	5962-XXXXXZZ(B or S)YY	QPL-38510 (Part 1 or 2)	MIL-BUL-103
New MIL-H-38534 Standardized Military Drawings	5962-XXXXXZZ(H or K)YY	QML-38534	MIL-BUL-103
New MIL-I-38535 Standardized Military Drawings	5962-XXXXXZZ(Q or V)YY	QML-38535	MIL-BUL-103
New 1.2.1 of MIL-STD-883 Standardized Military Drawings	5962-XXXXXZZ(M)YY	MIL-BUL-103	MIL-BUL-103

## 6.7 Sources of supply.

- 6.7.1 Sources of supply for device classes B and S. Sources of supply for device classes B and S are listed in QPL-38510.
- 6.7.2 <u>Sources of supply for device classes Q and V</u>. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DESC-EC and have agreed to this drawing.
- 6.7.3 <u>Approved sources of supply for device class M</u>. Approved sources of supply for class M are listed in MIL-BUL-103. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DESC-EC.

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